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- (57) **ABSTRACT**

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A semiconductor memory device may include a cell substrate, a mold structure including gate electrodes stacked on the cell substrate, a channel structures penetrating the mold structure; and a first cutting structure cutting some of the gate electrodes. The first cutting structure may include a first portion having a line shape extending in a first direction and a second portion having a line shape extending in a second direction. The first portion and the second portion may be alternately connected to form a zigzag shape. The first cutting structure may include a first side wall and a second side wall opposing the first side wall. A first point of the first side wall connected from the second portion to the first portion and a second point of the second side wall connected from the first portion to the second portion may be in corresponding channel structures among the channel structures.

